

1.5V Drive Pch MOSFET

RZR040P01

●Structure

Silicon P-channel MOSFET

●Features

- 1) Low on-resistance.
- 2) High power package.
- 3) Low voltage drive. (1.5V)

●Applications

Switching

●Packaging specifications

| Type | Package | Taping |
|-----------|------------------------------|--------|
| | Code | TL |
| | Basic ordering unit (pieces) | 3000 |
| RZR040P01 | | ○ |

●Absolute maximum ratings (Ta=25°C)

| Parameter | Symbol | Limits | Unit | |
|--------------------------------|------------|-------------|------|---|
| Drain-source voltage | V_{DSS} | -12 | V | |
| Gate-source voltage | V_{GSS} | ±10 | V | |
| Drain current | Continuous | I_D | ±4 | A |
| | Pulsed | I_{DP} *1 | ±16 | A |
| Source current (Body diode) | Continuous | I_S | -0.8 | A |
| | Pulsed | I_{SP} *1 | -16 | A |
| Total power dissipation | P_D *2 | 1.0 | W | |
| Channel temperature | T_{ch} | 150 | °C | |
| Range of Storage temperature | T_{stg} | -55 to +150 | °C | |

*1 $P_w \leq 10\mu s$, Duty cycle $\leq 1\%$

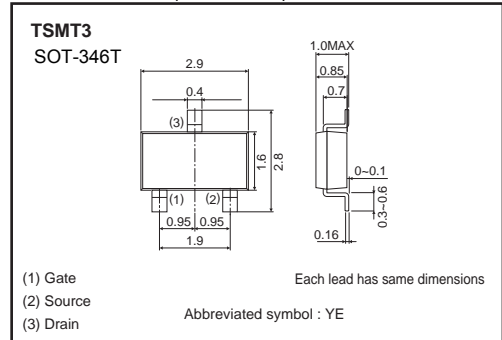
*2 When mounted on a ceramic board

●Thermal resistance

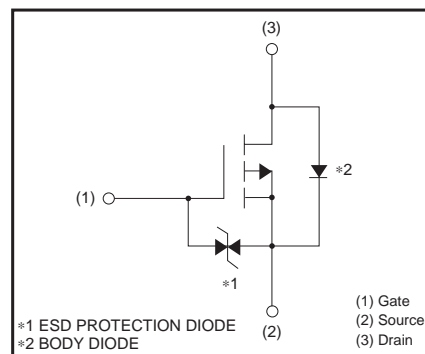
| Parameter | Symbol | Limits | Unit |
|--------------------|------------------|--------|--------|
| Channel to ambient | $R_{th(ch-a)}$ * | 125 | °C / W |

* When mounted on a ceramic board.

●Dimensions (Unit : mm)



●Inner circuit



●Electrical characteristics (Ta=25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|---|------------------------|------|------|------|------|---|
| Gate-source leakage | I _{GSS} | – | – | ±10 | μA | V _{GS} =±10V, V _{DS} =0V |
| Drain-source breakdown voltage | V _{(BR) DSS} | –12 | – | – | V | I _D = –1mA, V _{GS} =0V |
| Zero gate voltage drain current | I _{DSS} | – | – | –1 | μA | V _{DS} = –12V, V _{GS} =0V |
| Gate threshold voltage | V _{GS (th)} | –0.3 | – | –1.0 | V | V _{DS} = –6V, I _D = –1mA |
| Static drain-source on-state resistance | R _{DS (on)} * | – | 22 | 30 | mΩ | I _D = –4A, V _{GS} = –4.5V |
| | | – | 30 | 42 | mΩ | I _D = –2A, V _{GS} = –2.5V |
| | | – | 40 | 60 | mΩ | I _D = –2A, V _{GS} = –1.8V |
| | | – | 55 | 110 | mΩ | I _D = –0.8A, V _{GS} = –1.5V |
| Forward transfer admittance | Y _{fs} * | 6.5 | – | – | S | V _{DS} = –6V, I _D = –4A |
| Input capacitance | C _{iss} | – | 2350 | – | pF | V _{DS} = –6V |
| Output capacitance | C _{oss} | – | 310 | – | pF | V _{GS} =0V |
| Reverse transfer capacitance | C _{rss} | – | 280 | – | pF | f=1MHz |
| Turn-on delay time | t _{d (on)} * | – | 11 | – | ns | V _{DD} ≐ –6V |
| Rise time | t _r * | – | 70 | – | ns | I _D = –2A |
| Turn-off delay time | t _{d (off)} * | – | 380 | – | ns | V _{GS} = –4.5V |
| Fall time | t _f * | – | 210 | – | ns | R _L ≐ 3Ω |
| Total gate charge | Q _g * | – | 30 | – | nC | V _{DD} ≐ –6V R _L ≐ 1.5Ω |
| Gate-source charge | Q _{gs} * | – | 4.0 | – | nC | I _D = –4A R _G =10Ω |
| Gate-drain charge | Q _{gd} * | – | 3.5 | – | nC | V _{GS} = –4.5V |

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|-----------------|-------------------|------|------|------|------|---|
| Forward voltage | V _{SD} * | – | – | –1.2 | V | I _S = –4A, V _{GS} =0V |

*Pulsed

●Electrical characteristics curves

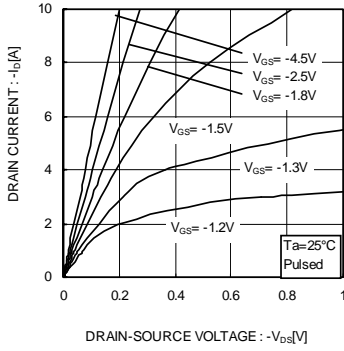


Fig.1 Typical output characteristics (I)

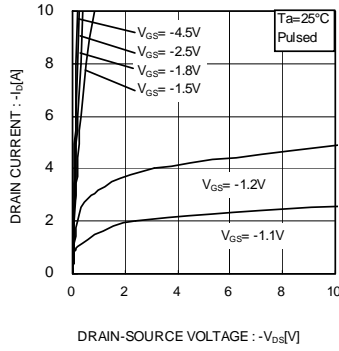


Fig.2 Typical output characteristics (II)

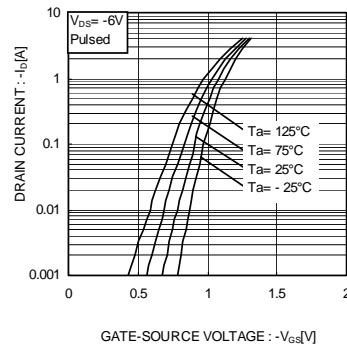


Fig.3 Typical Transfer Characteristics

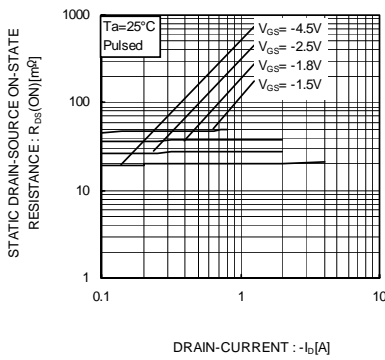


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (I)

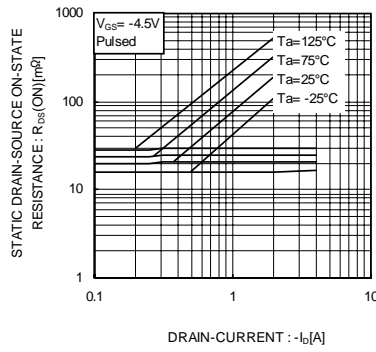


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current (II)

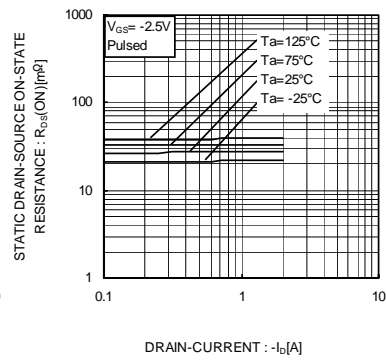


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current (III)

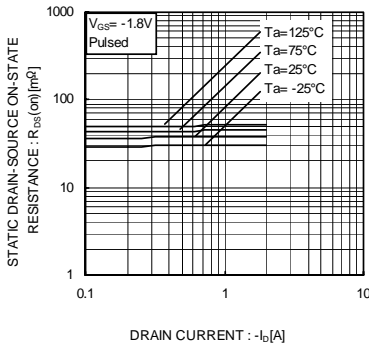


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (IV)

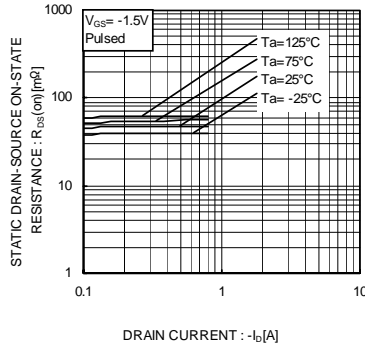


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (V)

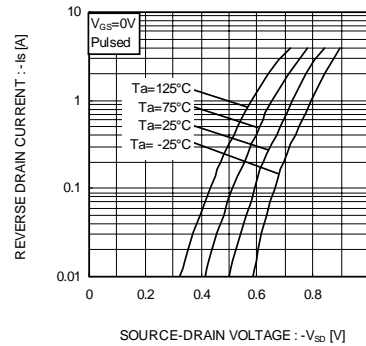


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

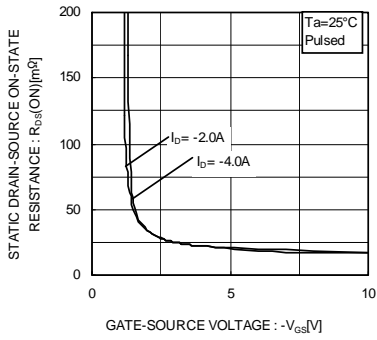


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

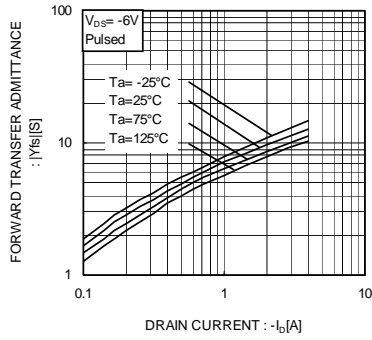


Fig.11 Forward Transfer Admittance vs. Drain Current

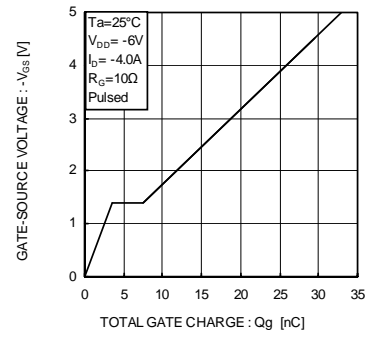


Fig.12 Dynamic Input Characteristics

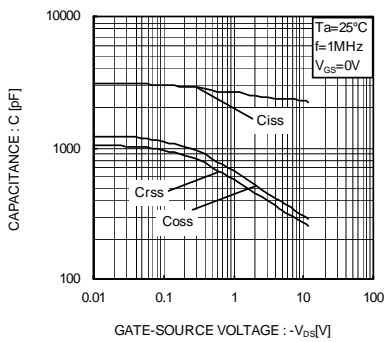


Fig.13 Typical Capacitance vs. Drain-Source Voltage

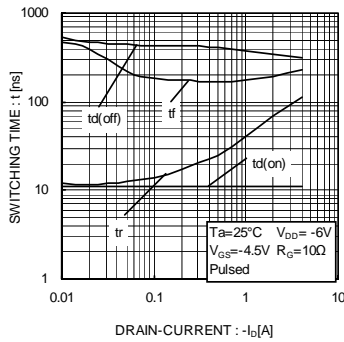


Fig.14 Switching Characteristics

●Measurement circuits

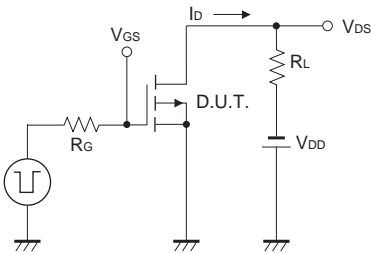


Fig.1-1 Switching Time Measurement Circuit

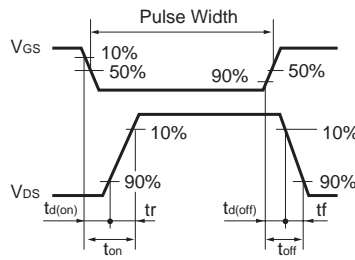


Fig.1-2 Switching Waveforms

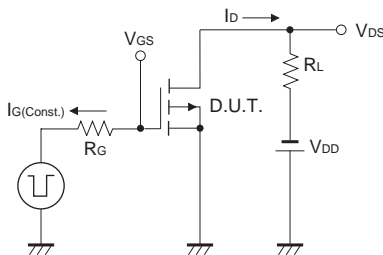


Fig.2-1 Gate Charge Measurement Circuit

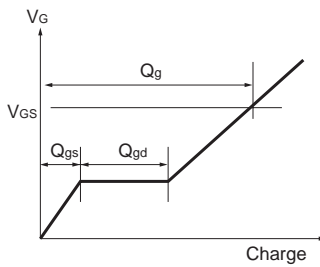


Fig.2-2 Gate Charge Waveform

●Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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